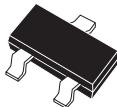


**CMPD4448****HIGH SPEED  
SWITCHING DIODE****SOT-23 CASE**

**Central**<sup>TM</sup>  
Semiconductor Corp.

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMPD4448 type is a ultra-high speed silicon switching diode manufactured by the epitaxial planar process, in an epoxy molded surface mount package, designed for high speed switching applications.

**Marking code is AAD.**

**MAXIMUM RATINGS (T<sub>A</sub>=25°C)**

	<b>SYMBOL</b>		<b>UNITS</b>
Continuous Reverse Voltage	V <sub>R</sub>	75	V
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	100	V
Continuous Forward Current	I <sub>F</sub>	250	mA
Peak Repetitive Forward Current	I <sub>FRM</sub>	250	mA
Forward Surge Current, tp=1 μsec.	I <sub>FSM</sub>	4000	mA
Forward Surge Current, tp=1 sec.	I <sub>FSM</sub>	1000	mA
Power Dissipation	P <sub>D</sub>	350	mW
Operating and Storage			
Junction Temperature	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C
Thermal Resistance	Θ <sub>JA</sub>	357	°C/W

**ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C unless otherwise noted)**

<b>SYMBOL</b>	<b>TEST CONDITIONS</b>	<b>MIN</b>	<b>MAX</b>	<b>UNITS</b>
V <sub>BR</sub>	I <sub>R</sub> =5.0μA	75		V
V <sub>BR</sub>	I <sub>R</sub> =100μA	100		V
I <sub>R</sub>	V <sub>R</sub> =20V		25	nA
V <sub>F</sub>	I <sub>F</sub> =5.0mA	0.62	0.72	V
V <sub>F</sub>	I <sub>F</sub> =100mA		1.0	V
C <sub>T</sub>	V <sub>R</sub> =0, f=1 MHz		4.0	pF
t <sub>rr</sub>	I <sub>R</sub> =I <sub>F</sub> =10mA, R <sub>L</sub> =100Ω, Rec. to 1.0mA		4.0	ns

All dimensions in inches (mm).

